

Product Overview

The CMD246 is a wideband GaAs MMIC low phase noise amplifier ideally suited for military, space and communications systems. At 16 GHz the device delivers 17 dB of gain, a saturated output power of +18 dBm and a noise figure of 3.5 dB. Also with an input signal of 10 GHz the amplifier provides low phase noise performance of -165 dBc/Hz at 10 kHz offset. The CMD246 is a 50 ohm matched design which eliminates the need for RF port matching. The CMD246 offers full passivation for increased reliability and moisture protection.

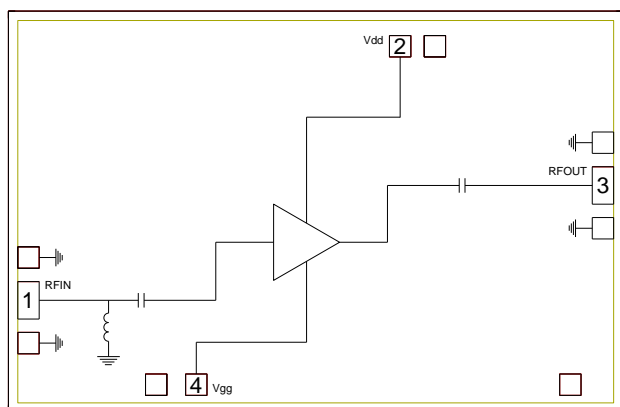
Key Features

- Wide Bandwidth
- Low Phase Noise
- Low Current Consumption
- Small Die Size

Ordering Information

Part No.	Description
CMD246	8-22 GHz Low Phase Noise Amplifier, 50 Piece Gel Pack

Functional Block Diagram



Electrical Performance ($V_{dd} = 5.0 \text{ V}$, $V_{gg} = 3.0 \text{ V}$, $T_A = 25^\circ \text{C}$, $F = 16 \text{ GHz}$)

Parameter	Min	Typ	Max	Units
Frequency Range		8 - 25		GHz
Gain		17		dB
Input Return Loss		8		dB
Output Return Loss		13		dB
Noise Figure		3.5		dB
Output P1dB		13		dBm
Saturated Output Power		18		dBm
Phase Noise @ 10 kHz Offset		-165		dBc/Hz
Supply Current		48		mA

Absolute Maximum Ratings

Parameter	Rating
Drain Voltage, V_{dd}	8.0 V
Gate Voltage, V_{gg}	5.0 V
RF Input Power	+15 dBm
Channel Temperature, T_{ch}	150 °C
Power Dissipation, P_{diss}	422 mW
Thermal Resistance, θ_{JC}	154 °C/W
Operating Temperature	-55 to 85 °C
Storage Temperature	-55 to 150 °C

Exceeding any one or combination of the maximum ratings may cause permanent damage to the device.

Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
V_{dd}	3.0	5.0	7.0	V
I_{dd}		48		mA
V_{gg}	0	3.0	4.0	V

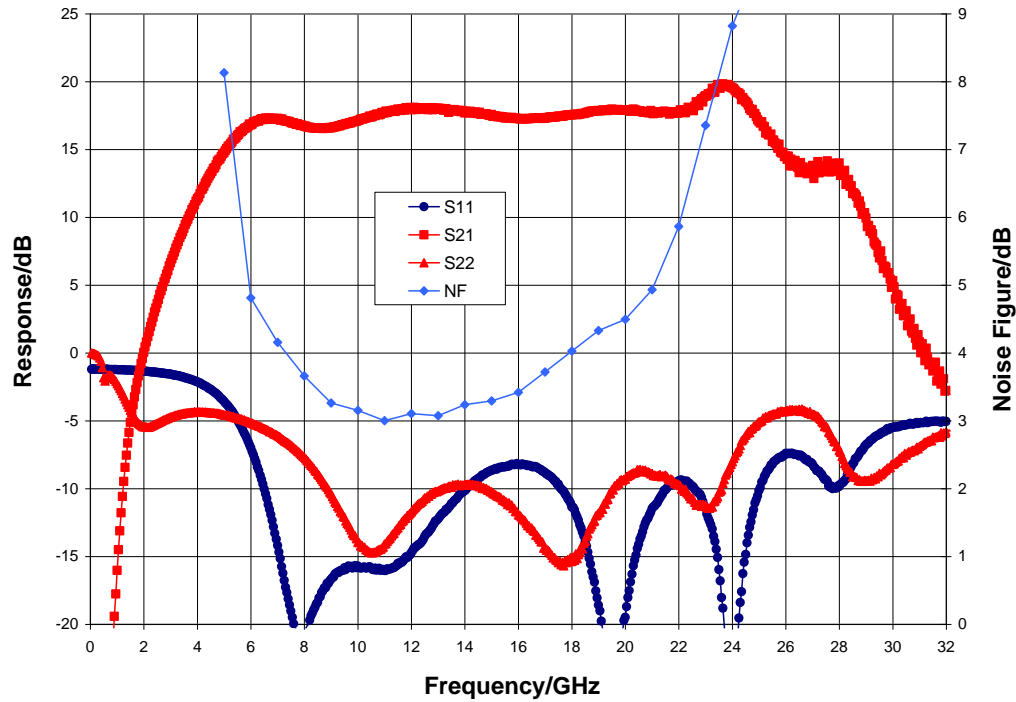
Electrical performance is measured at specific test conditions.
Electrical specifications are not guaranteed over all recommended operating conditions.

Electrical Specifications ($V_{dd} = 5.0$ V, $V_{gg} = 3.0$ V, $T_A = 25$ °C)

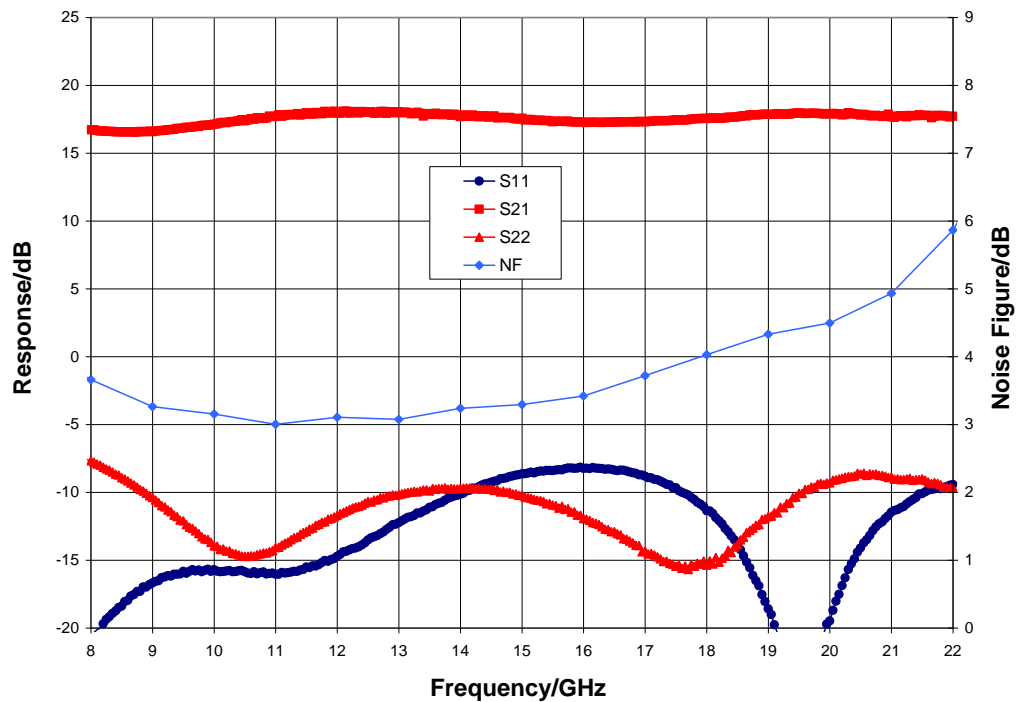
Parameter	Min	Typ	Max	Min	Typ	Max	Units
Frequency Range		8 - 16			16 - 22		GHz
Gain	14	17	21	14	18	21	dB
Noise Figure		3.5			4.5		dB
Input Return Loss		10			10		dB
Output Return Loss		10			10		dB
Output P1dB	10	16		6	12		dBm
Saturated Output Power		20			15		dBm
Output IP3		25			24		dBm
Phase Noise @ 10 kHz Offset		-165			-165		dBc/Hz
Supply Current	33	48	63	33	48	63	mA

Typical Performance

Broadband Performance, $V_{dd} = 5.0 \text{ V}$, $V_{gg} = 3.0 \text{ V}$, $I_{dd} = 48 \text{ mA}$, $T_A = 25^\circ \text{C}$

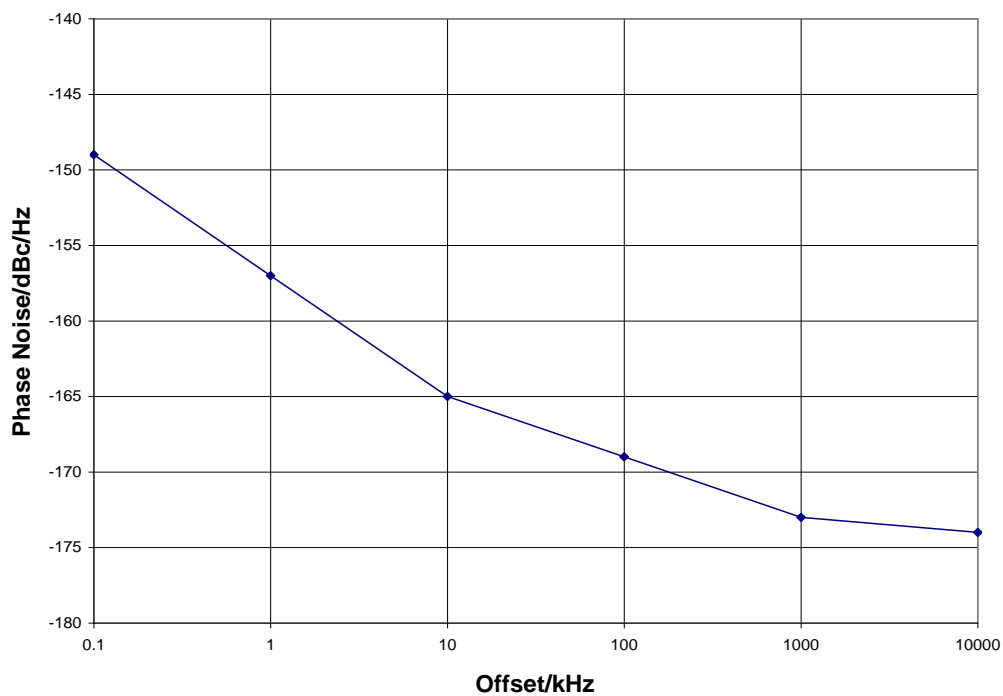


Narrow-band Performance, $V_{dd} = 5.0 \text{ V}$, $V_{gg} = 3.0 \text{ V}$, $I_{dd} = 48 \text{ mA}$, $T_A = 25^\circ \text{C}$

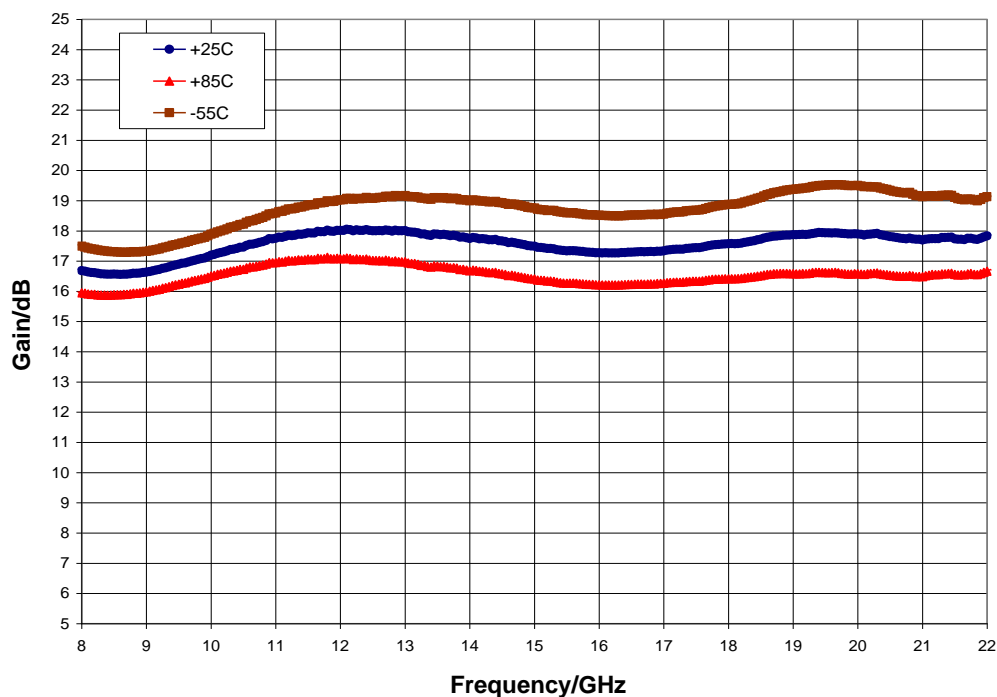


Typical Performance

Additive Phase Noise @ P_{sat} , $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$

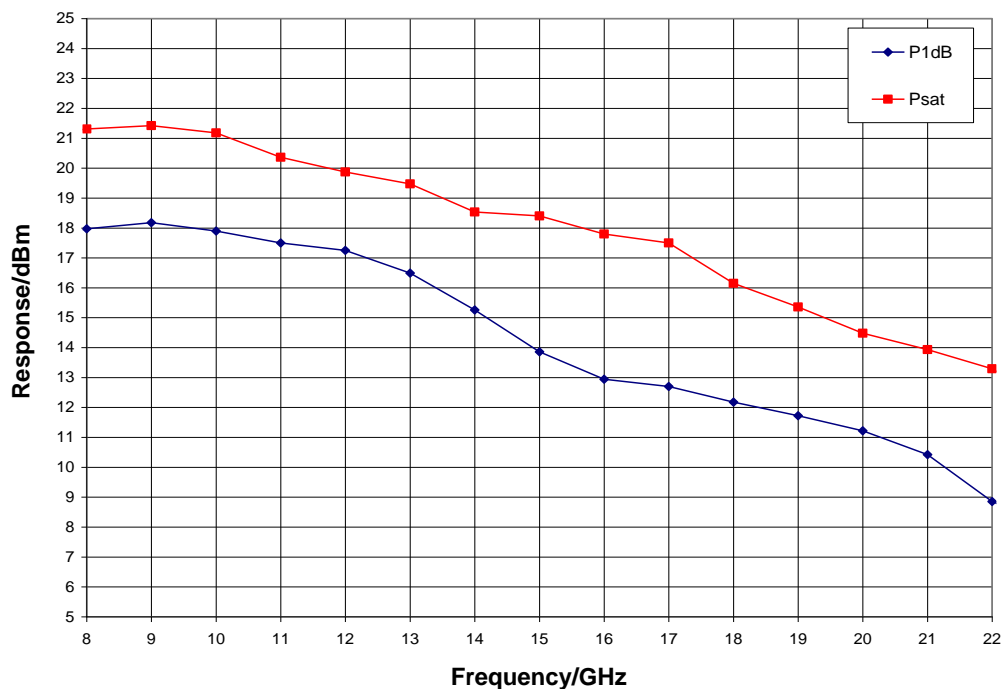


Gain vs. Temperature, $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$

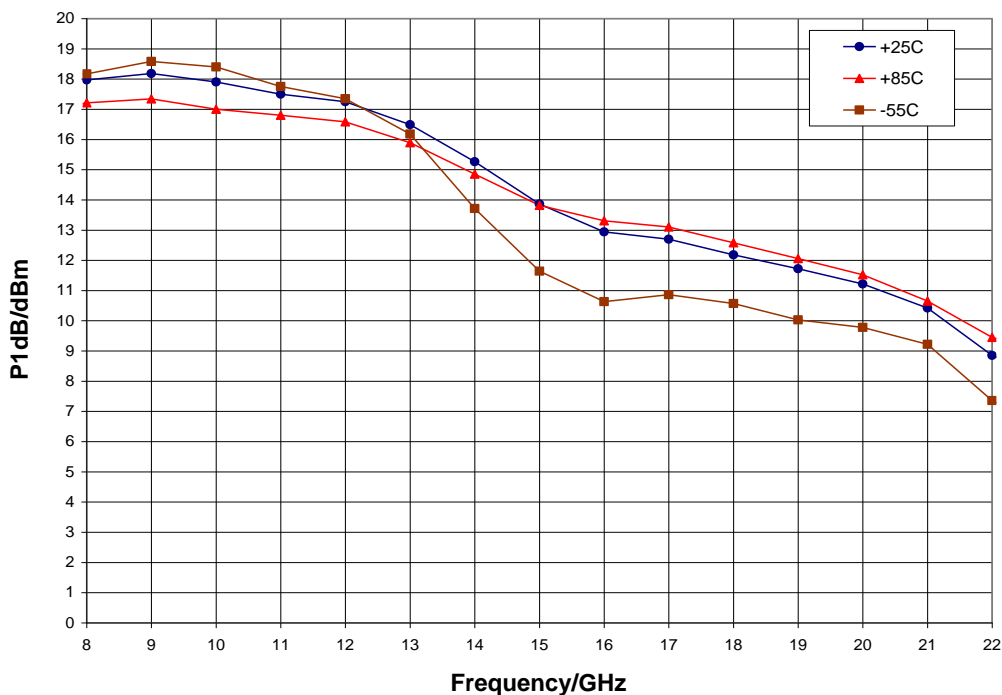


Typical Performance

Output Power, $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$

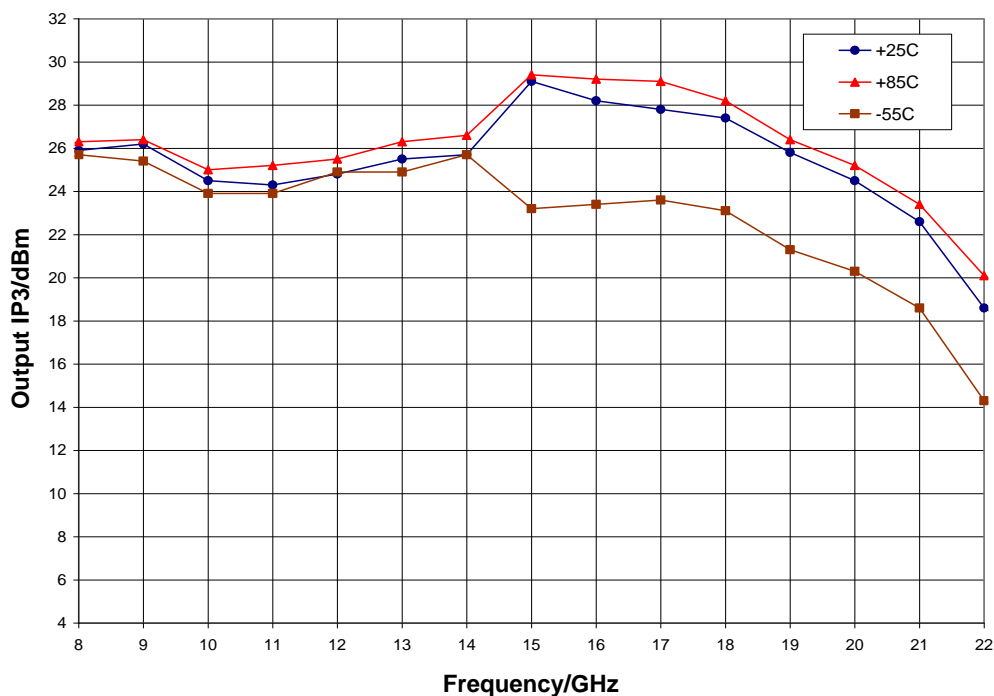


P1dB vs. Temperature, $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$

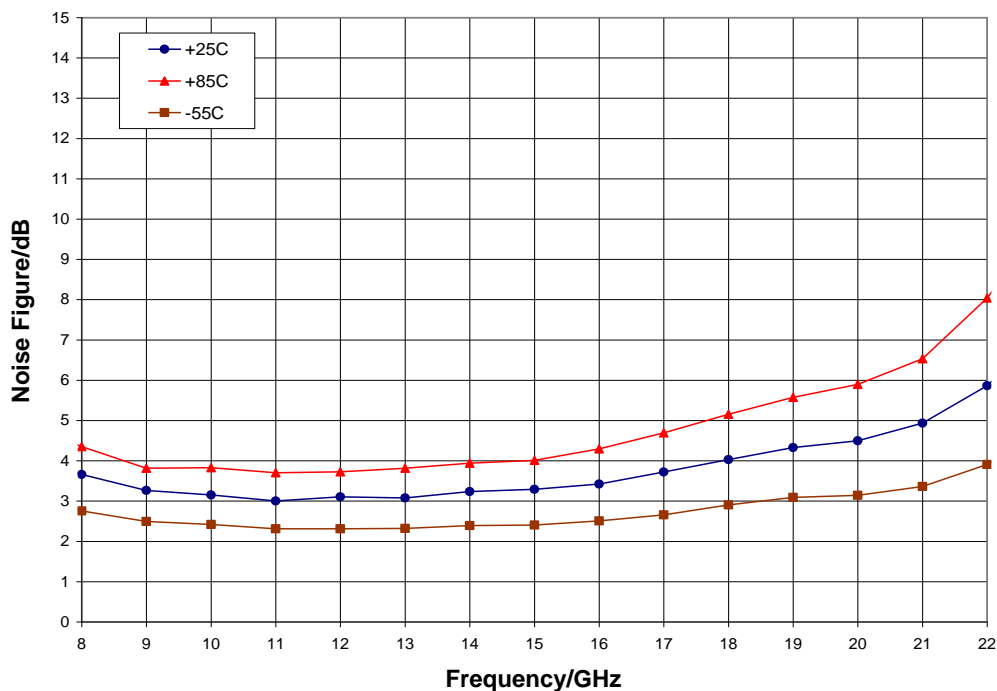


Typical Performance

Output IP3 vs. Temperature, $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$

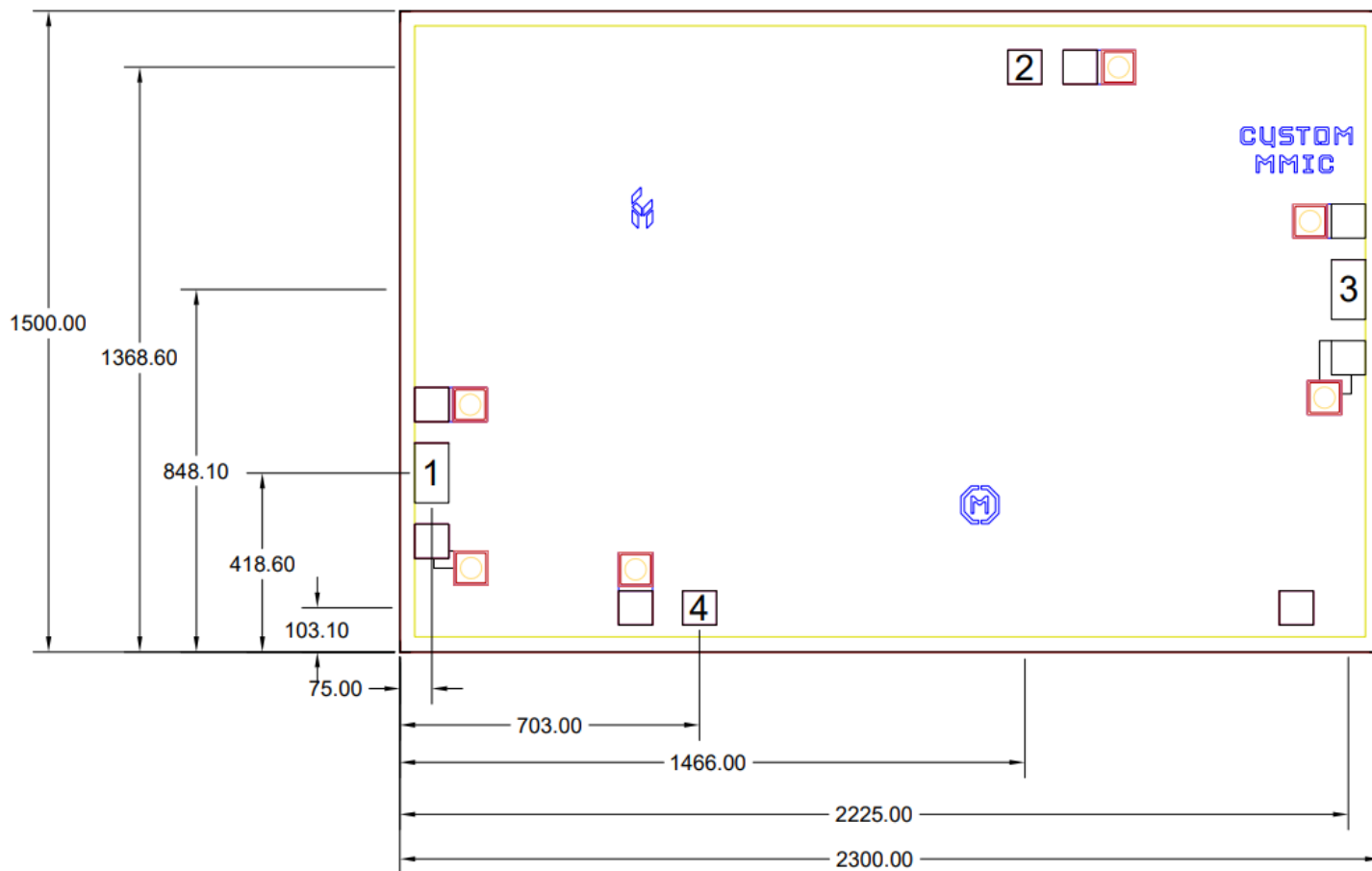


Noise Figure vs. Temperature, $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$



Mechanical Information

Die Outline (all dimensions in microns)

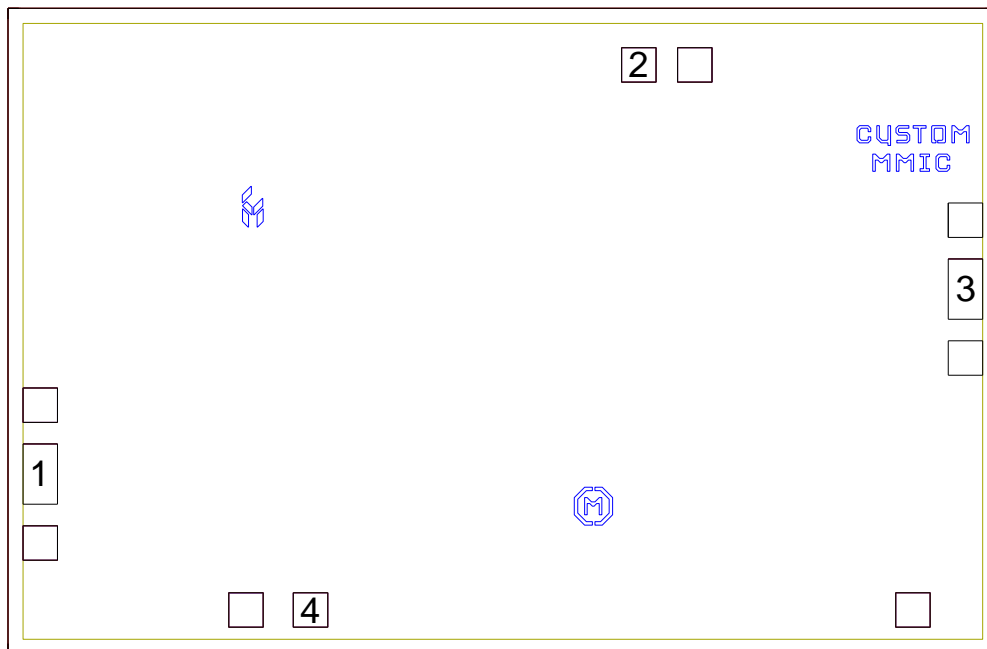


Notes:

1. No connection required for unlabeled pads
2. Backside is RF and DC ground
3. Backside and bond pad metal: Gold
4. Die is 100 microns thick
5. DC bond pads (2, 4) are 80 x 80 microns
6. RF bond pads (1, 3) are 80 x 140 microns

Pad Description

Pad Diagram



Functional Description

Pad	Function	Description	Schematic
1	RF in	DC coupled and 50 ohm matched	
2	V _{dd}	Power supply voltage Decoupling and bypass caps required	
3	RF out	DC blocked and 50 ohm matched	
4	V _{gg}	Power supply voltage Decoupling and bypass caps required	
Backside	Ground	Connect to RF / DC ground	

Applications Information

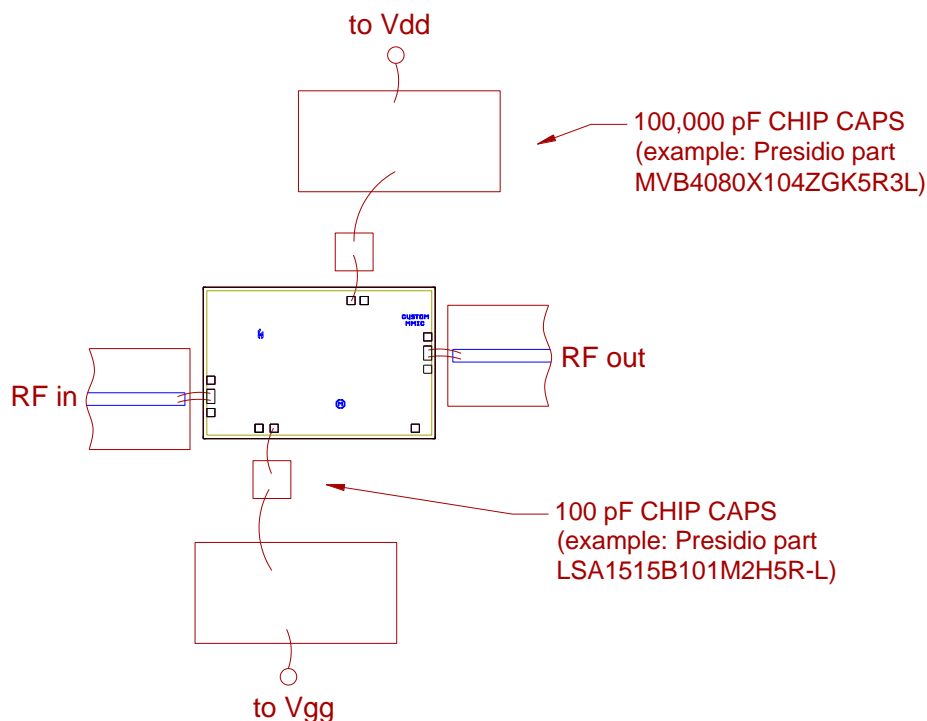
Assembly Guidelines

The backside of the CMD246 is RF ground. Die attach should be accomplished with electrically and thermally conductive epoxy only. Eutectic attach is not recommended. Standard assembly procedures should be followed for high frequency devices. The top surface of the semiconductor should be made planar to the adjacent RF transmission lines, and the RF decoupling capacitors placed in close proximity to the DC connections on chip.

RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized. The RF input and output require a double bond wire as shown.

The semiconductor is 100 μm thick and should be handled by the sides of the die or with a custom collet. Do not make contact directly with the die surface as this will damage the monolithic circuitry. Handle with care.

Assembly Diagram



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

Applications Information

Biasing and Operation

The CMD246 is biased with a positive drain supply and a positive gate supply. Performance is optimized when the drain voltage is set to +5.0 V. The recommended gate voltage is +3.0 V.

Turn ON procedure:

1. Apply drain voltage V_{dd} and set to +5 V
2. Apply gate voltage V_{gg} and set to +3 V

Turn OFF procedure:

1. Turn off gate voltage V_{gg}
2. Turn off drain voltage V_{dd}

RF power can be applied at any time.

Handling Precautions

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	Class 1A	ESDA / JEDEC JS-001-2012



Caution!
 ESD-Sensitive Device

RoHS Compliance

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Lead Free
- Antimony Free
- TBBP-A (C₁₅H₁₂Br₄O₂) Free
- SVHC Free
- Halogen Free
- PFOS Free

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

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